Ana M Sanchez

List of Publications by Year
in descending order

219 papers	5,689 citations	94433 37 h-index	98798 67 g-index
220 all docs	220 docs citations	220 times ranked	8732 citing authors

#	Article	IF	Citations
1	Vibrational and electronic structures of tin selenide nanowires confined inside carbon nanotubes. Synthetic Metals, 2022, 284, 116968.	3.9	9
2	Thermally-driven formation method for growing (quantum) dots on sidewalls of self-catalysed thin nanowires. Nanoscale Horizons, 2022, 7, 311-318.	8.0	2
3	Ferroelectric incommensurate spin crystals. Nature, 2022, 602, 240-244.	27.8	30
4	Atomic-scale investigation of the reversible Î±- to Ï‰-phase lithium ion charge â€“ discharge characteristics of electrodeposited vanadium pentoxide nanobelts. Journal of Materials Chemistry A, 2022, 10, 8515-8527.	10.3	4
5	Te-doped selective-area grown InAs nanowires for superconducting hybrid devices. Physical Review Materials, 2022, 6, .	2.4	1
6	Bi incorporation and segregation in the MBE-grown GaAs-(Ga,Al)As-Ga(As,Bi) coreâ€“shell nanowires. Scientific Reports, 2022, 12, 6007.	3.3	1
7	Long-Term Stability and Optoelectronic Performance Enhancement of InAsP Nanowires with an Ultrathin InP Passivation Layer. Nano Letters, 2022, 22, 3433-3439.	9.1	3
8	Multiple radial phosphorus segregations in GaAsP core-shell nanowires. Nano Research, 2021, 14, 157-164.	10.4	3
9	Fully in situ Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. Nanoscale Advances, 2021, 3, 1413-1421.	4.6	11
10	Atomic and electronic structure of two-dimensional Mo_{(1â^’} _x)W _x S₂ alloys. JPhys Materials, 2021, 4, 025004.	4.2	7
11	Real-space observation of ferroelectrically induced magnetic spin crystal in SrRuO3. Nature Communications, 2021, 12, 2007.	12.8	21
12	Quantum Transport of the 2D Surface State in a Nonsymmorphic Semimetal. Nano Letters, 2021, 21, 4887-4893.	9.1	15
13	Defect-Free Axially Stacked GaAs/GaAsP Nanowire Quantum Dots with Strong Carrier Confinement. Nano Letters, 2021, 21, 5722-5729.	9.1	14
14	Robust Protection of IIIâ€“V Nanowires in Water Splitting by a Thin Compact TiO₂ Layer. ACS Applied Materials & Interfaces, 2021, 13, 30950-30958.	8.0	12
15	Self-Catalyzed AlGaAs Nanowires and AlGaAs/GaAs Nanowire-Quantum Dots on Si Substrates. Journal of Physical Chemistry C, 2021, 125, 14338-14347.	3.1	5
16	All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.	2.8	23
17	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. Journal of Lightwave Technology, 2020, 38, 240-248.	4.6	46
18	Zn₂GeO₄/SnO₂ Nanowire Heterostructures Driven by Plateauâ€“Rayleigh Instability. Crystal Growth and Design, 2020, 20, 506-513.	3.0	9

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19	Checked patterned elemental distribution in AlGaAs nanowire branches via vaporâ€“liquidâ€“solid growth. Nanoscale, 2020, 12, 15711-15720.	5.6	1
20	Polarization Screening Mechanisms at La_{0.7}Sr_{0.3}MnO₃â€“PbTiO₃ Interfaces. ACS Applied Materials & Interfaces, 2020, 12, 10657-10663.	8.0	7
21	Inversion Boundary Annihilation in GaAs Monolithically Grown on Onâ€Axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.	7.3	22
22	Hard-Gap Spectroscopy in a Self-Defined Mesoscopic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>In</mml:mi><mml:mi>As</mml:mi></mml:mrow></mml:math>/<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Al</mml:mi></mml:math>Nanowire Josephson Junction. Physical Review Applied, 2020, 14, .	3.8	4
23	Rapidly self-deoxygenating controlled radical polymerization in water via in situ disproportionation of Cu(<scp>i</scp>). Chemical Science, 2020, 11, 5257-5266.	7.4	26
24	High yield production of ultrathin fibroid semiconducting nanowire of Ta2Pd3Se8. Nano Research, 2020, 13, 1627-1635.	10.4	16
25	Ge incorporation in gallium oxide nanostructures grown by thermal treatment. Journal of Materials Science, 2020, 55, 11431-11438.	3.7	5
26	A comparative study of graphite and silicon as suitable substrates for the self-catalysed growth of InAs nanowires by MBE. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	2
27	Heterostructure and Q-factor engineering for low-threshold and persistent nanowire lasing. Light: Science and Applications, 2020, 9, 43.	16.6	26
28	Droplet manipulation and horizontal growth of high-quality self-catalysed GaAsP nanowires. Nano Today, 2020, 34, 100921.	11.9	3
29	Emergent Antipolar Phase in BiFeO₃â€“La_{0.7}Sr_{0.3}MnO₃ Superlattice. Nano Letters, 2020, 20, 6045-6050.	9.1	12
30	Enhanced Superconductivity in Few-Layer TaS₂ due to Healing by Oxygenation. Nano Letters, 2020, 20, 3808-3818.	9.1	23
31	Preferred growth direction of IIIâ€“V nanowires on differently oriented Si substrates. Nanotechnology, 2020, 31, 475708.	2.6	8
32	Structural and photoelectric properties of tensile strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BiFeO</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math> Physical Review Materials, 2020, 4, .	2.4	3
33	GaAsP nanowires containing intentional and self-forming quantum dots. , 2020, , .		0
34	Control of complex quantum structures in droplet epitaxy. Semiconductor Science and Technology, 2019, 34, 095011.	2.0	5
35	InAs/GaAs quantum dot solar cells with quantum dots in the base region. IET Optoelectronics, 2019, 13, 215-217.	3.3	9
36	Strain-gradient mediated local conduction in strained bismuth ferrite films. Nature Communications, 2019, 10, 2791.	12.8	28

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37	Flexible Memristors Based on Single-Crystalline Ferroelectric Tunnel Junctions. ACS Applied Materials & Interfaces, 2019, 11, 23313-23319.	8.0	56
38	Self-Formed Quantum Wires and Dots in GaAsPâ€“GaAsP Coreâ€“Shell Nanowires. Nano Letters, 2019, 19, 4158-4165.	9.1	15
39	Defect Dynamics in Self-Catalyzed IIIâ€“V Semiconductor Nanowires. Nano Letters, 2019, 19, 4574-4580.	9.1	5
40	Highly Strained IIIâ€“Vâ€“V Coaxial Nanowire Quantum Wells with Strong Carrier Confinement. ACS Nano, 2019, 13, 5931-5938.	14.6	19
41	Unprecedented New Crystalline Forms of SnSe in Narrow to Medium Diameter Carbon Nanotubes. Nano Letters, 2019, 19, 2979-2984.	9.1	34
42	Thin Ge buffer layer on silicon for integration of III-V on silicon. Journal of Crystal Growth, 2019, 514, 109-113.	1.5	17
43	Engineering the Side Facets of Vertical [100] Oriented InP Nanowires for Novel Radial Heterostructures. Nanoscale Research Letters, 2019, 14, 399.	5.7	9
44	Growth and Fabrication of Highâ€Quality Single Nanowire Devices with Radial pâ€“iâ€“n Junctions. Small, 2019, 15, 1803684.	10.0	16
45	Direct observation of tunnelled intergrowth in SnO₂/Ga₂O₃ complex nanowires. Nanotechnology, 2019, 30, 054004.	2.6	2
46	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (0â€“0â€“1) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.	1.5	31
47	Quantitative Highâ€Dynamicâ€Range Electron Diffraction of Polar Nanodomains in Pb₂ScTaO₆. Advanced Materials, 2019, 31, e1806498.	21.0	12
48	Bi-ferroic memristive properties of multiferroic tunnel junctions. Applied Physics Letters, 2018, 112, 102905.	3.3	15
49	Stable Defects in Semiconductor Nanowires. Nano Letters, 2018, 18, 3081-3087.	9.1	16
50	Highâ€Responsivity Photodetection by a Selfâ€Catalyzed Phaseâ€Pure pâ€GaAs Nanowire. Small, 2018, 14, e1704429.	10.0	54
51	Novel Typeâ€II InAs/AlSb Coreâ€“Shell Nanowires and Their Enhanced Negative Photocurrent for Efficient Photodetection. Advanced Functional Materials, 2018, 28, 1705382.	14.9	36
52	Room-Temperature Mid-Infrared Emission from Faceted InAsSb Multi Quantum Wells Embedded in InAs Nanowires. Nano Letters, 2018, 18, 235-240.	9.1	11
53	Doping of Self-Catalyzed Nanowires under the Influence of Droplets. Nano Letters, 2018, 18, 81-87.	9.1	24
54	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	3.2	15

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55	Hybrid IIIâ€“V/IV Nanowires: High-Quality Ge Shell Epitaxy on GaAs Cores. Nano Letters, 2018, 18, 6397-6403.	9.1	6
56	Growth and characterisation of MnSb(0â€¯0â€¯0â€¯1)/InGaAs(1â€¯1â€¯1)A epitaxial films. Journal of Crystal Growth, 2018, 498, 391-398.	1.5	6
57	Indium rich clusters in MOCVD InGaN/GaN: high resolution electron microscopy study and finite element modelling. , 2018, , 61-64.		0
58	Multiple atomic configurations of inversion domain boundaries in GaN grown on (111)Si. , 2018, , 333-336.		0
59	Atomic Defects and Doping of Monolayer NbSe₂. ACS Nano, 2017, 11, 2894-2904.	14.6	63
60	Optically efficient InAsSb nanowires for silicon-based mid-wavelength infrared optoelectronics. Nanotechnology, 2017, 28, 105710.	2.6	19
61	Influence of droplet size on the growth of high-quality self-catalyzed GaAsP nanowires. , 2017, , .		0
62	GaAsP nanowires and nanowire devices grown on silicon substrates. Proceedings of SPIE, 2017, , .	0.8	3
63	Optimization of self-catalyzed InAs Nanowires on flexible graphite for photovoltaic infrared photodetectors. Scientific Reports, 2017, 7, 46110.	3.3	18
64	Antiferroelectric Tunnel Junctions. Advanced Electronic Materials, 2017, 3, 1700126.	5.1	24
65	Ten-Fold Enhancement of InAs Nanowire Photoluminescence Emission with an InP Passivation Layer. Nano Letters, 2017, 17, 3629-3633.	9.1	19
66	Nonradiative Step Facets in Semiconductor Nanowires. Nano Letters, 2017, 17, 2454-2459.	9.1	17
67	Shape Engineering Driven by Selective Growth of SnO₂ on Doped Ga₂O₃ Nanowires. Nano Letters, 2017, 17, 515-522.	9.1	26
68	3D and 2D growth of SnO₂ nanostructures on Ga₂O₃ nanowires: synthesis and structural characterization. CrystEngComm, 2017, 19, 6127-6132.	2.6	6
69	Comparative Study of RESURF Si/SiC LDMOSFETs for High-Temperature Applications Using TCAD Modeling. IEEE Transactions on Electron Devices, 2017, 64, 3713-3718.	3.0	13
70	Growth of Pure Zinc-Blende GaAs(P) Coreâ€“Shell Nanowires with Highly Regular Morphology. Nano Letters, 2017, 17, 4946-4950.	9.1	22
71	Retarding oxidation of copper nanoparticles without electrical isolation and the size dependence of work function. Nature Communications, 2017, 8, 1894.	12.8	78
72	A decision making model to evaluate the reputation in social networks using HFLTS. , 2017, , .		3

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73	Metalorganic vapor phase epitaxy growth, transmission electron microscopy, and magneto-optical spectroscopy of individual InAsxP1â^'x/Ga0.5In0.5P quantum dots. Physical Review Materials, 2017, 1, .	2.4	1
74	TEM Study of the Structural Properties of Nanowires Based on Cd, Zn, Te grown by MBE on Silicon Substrates. Acta Physica Polonica A, 2017, 131, 1399-1405.	0.5	4
75	Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co2FeSi0.5Al0.5/Ge(111). Scientific Reports, 2016, 6, 37282.	3.3	18
76	The antiphase boundary in half-metallic Heusler alloy Co2Fe(Al,Si): atomic structure, spin polarization reversal, and domain wall effects. Applied Physics Letters, 2016, 109, .	3.3	9
77	On the vertical stacking in semiconducting WSe₂ bilayers. Materials Science and Technology, 2016, 32, 226-231.	1.6	3
78	Growth of high-quality self-catalyzed core-shell GaAsP nanowires on Si substrates. Proceedings of SPIE, 2016, , .	0.8	0
79	Si1-x Ge x /Si Interface Profiles Measured to Sub-Nanometer Precision Using uleSIMS Energy Sequencing. Journal of the American Society for Mass Spectrometry, 2016, 27, 1694-1702.	2.8	5
80	Direct Fabrication of Functional Ultrathin Single-Crystal Nanowires from Quasi-One-Dimensional van der Waals Crystals. Nano Letters, 2016, 16, 6188-6195.	9.1	37
81	Polarization curling and flux closures in multiferroic tunnel junctions. Nature Communications, 2016, 7, 13484.	12.8	58
82	Optimisation of anatase TiO2 thin film growth on LaAlO3(0 0 1) using pulsed laser deposition. Applied Surface Science, 2016, 388, 684-690.	6.1	8
83	Defect-Free Self-Catalyzed GaAs/GaAsP Nanowire Quantum Dots Grown on Silicon Substrate. Nano Letters, 2016, 16, 504-511.	9.1	42
84	Coexistence of optically active radial and axial CdTe insertions in single ZnTe nanowire. Nanoscale, 2016, 8, 5720-5727.	5.6	7
85	Low Leakage-Current InAsSb Nanowire Photodetectors on Silicon. Nano Letters, 2016, 16, 182-187.	9.1	63
86	Influence of Droplet Size on the Growth of Self-Catalyzed Ternary GaAsP Nanowires. Nano Letters, 2016, 16, 1237-1243.	9.1	49
87	Nanoscale Inhomogeneous Superconductivity in Fe(Te1â€“xSex) Probed by Nanostructure Transport. ACS Nano, 2016, 10, 429-435.	14.6	6
88	The effect of atomic structure on interface spin-polarization of half-metallic spin valves: Co2MnSi/Ag epitaxial interfaces. Applied Physics Letters, 2015, 107, .	3.3	13
89	Imaging the dynamics of polar nanoregions in PbSc0.5Ta0.5O3using transmission electron microscopy and 'digital' electron diffraction. Acta Crystallographica Section A: Foundations and Advances, 2015, 71, s66-s66.	0.1	0
90	Growth of complex SiGe/Ge superlattices by reduced pressure chemical vapour deposition at low temperature. Semiconductor Science and Technology, 2015, 30, 114009.	2.0	5

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91	Structural, optical and vibrational properties of self-assembled Pbn+1(Ti1â^'xFex)nO3n+1â^Î´ Ruddlesden-Popper superstructures. Scientific Reports, 2015, 5, 7719.	3.3	8
92	Morphology â€“ composition correlations in carbon nanotubes synthesised with nitrogen and phosphorus containing precursors. Physical Chemistry Chemical Physics, 2015, 17, 2137-2142.	2.8	6
93	Effect of annealing in the Sb and In distribution of type II GaAsSb-capped InAs quantum dots. Semiconductor Science and Technology, 2015, 30, 114006.	2.0	12
94	Sb-Induced Phase Control of InAsSb Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2015, 15, 1109-1116.	9.1	55
95	Artefacts in geometric phase analysis of compound materials. Ultramicroscopy, 2015, 157, 91-97.	1.9	64
96	Realization of Vertically Aligned, Ultrahigh Aspect Ratio InAsSb Nanowires on Graphite. Nano Letters, 2015, 15, 4348-4355.	9.1	37
97	Osmium Atoms and Os₂ Molecules Move Faster on Selenium-Doped Compared to Sulfur-Doped Boronic Graphenic Surfaces. Chemistry of Materials, 2015, 27, 5100-5105.	6.7	14
98	Polarity-Driven Quasi-3-Fold Composition Symmetry of Self-Catalyzed IIIâ€“Vâ€“V Ternary Coreâ€“Shell Nanowires. Nano Letters, 2015, 15, 3128-3133.	9.1	39
99	Microscopy of Semiconducting Materials 2015. Semiconductor Science and Technology, 2015, 30, 110301.	2.0	2
100	Nanomaterials of the Topological Crystalline Insulators, Pb_{1â€“x}Sn_xTe and Pb_{1â€“x}Sn_xSe. Crystal Growth and Design, 2015, 15, 5202-5206.	3.0	13
101	Exploiting nucleobase-containing materials â€“ from monomers to complex morphologies using RAFT dispersion polymerization. Polymer Chemistry, 2015, 6, 106-117.	3.9	79
102	EPITAXIAL GROWTH OF CUBIC MnSb ON GaAs AND InGaAs(111). Spin, 2014, 04, 1440025.	1.3	5
103	Structural reorganization of cylindrical nanoparticles triggered by polylactide stereocomplexation. Nature Communications, 2014, 5, 5746.	12.8	125
104	Optimal growth and thermal stability of crystalline Be0.25Zn0.75O alloy films on Al2O3(0001). Applied Physics Letters, 2014, 104, .	3.3	7
105	Selfâ€catalysed growth of InAs nanowires on bare Si substrates by droplet epitaxy. Physica Status Solidi - Rapid Research Letters, 2014, 8, 658-662.	2.4	10
106	Designing a compact Genetic fuzzy rule-based system for one-class classification. , 2014, , .		3
107	Bismuth incorporation and the role of ordering in GaAsBi/GaAs structures. Nanoscale Research Letters, 2014, 9, 23.	5.7	56
108	Fabrication of crystals from single metal atoms. Nature Communications, 2014, 5, 3851.	12.8	31

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109	Lateral heterojunctions within monolayer MoSe2â€“WSe2 semiconductors. Nature Materials, 2014, 13, 1096-1101.	27.5	872
110	Graphitic platform for self-catalysed InAs nanowires growth by molecular beam epitaxy. Nanoscale Research Letters, 2014, 9, 321.	5.7	11
111	Design rules for dislocation filters. Journal of Applied Physics, 2014, 116, .	2.5	55
112	Wafer-Scale Fabrication of Self-Catalyzed 1.7 eV GaAsP Coreâ€“Shell Nanowire Photocathode on Silicon Substrates. Nano Letters, 2014, 14, 2013-2018.	9.1	58
113	Weak mismatch epitaxy and structural Feedback in graphene growth on copper foil. Nano Research, 2013, 6, 99-112.	10.4	73
114	Structural and magnetic properties of pulsed laser deposited SrRuO3/CoFe2O4/La2/3Sr1/3MnO3 magnetic oxide heterostructures on SrTiO3(001) and MgO(001). Applied Physics A: Materials Science and Processing, 2013, 110, 889-894.	2.3	2
115	Rapid thermal annealing and photoluminescence of type-II GaSb single monolayer quantum dot stacks. Journal Physics D: Applied Physics, 2013, 46, 305104.	2.8	4
116	A new approach to high resolution, high contrast electron microscopy of macromolecular block copolymer assemblies. Soft Matter, 2013, 9, 3741.	2.7	12
117	Long-Wavelength Photoluminescence from Stacked Layers of High-Quality Type-II GaSb/GaAs Quantum Rings. Crystal Growth and Design, 2013, 13, 1226-1230.	3.0	15
118	High-Accuracy Analysis of Nanoscale Semiconductor Layers Using Beam-Exit Ar-Ion Polishing and Scanning Probe Microscopy. ACS Applied Materials & Interfaces, 2013, 5, 3241-3245.	8.0	17
119	IIIâ€“V quantum light source and cavity-QED on Silicon. Scientific Reports, 2013, 3, 1239.	3.3	33
120	Compositional analysis of InAs-GaAs-GaSb heterostructures by Low-Loss Electron Energy Loss Spectroscopy. Journal of Physics: Conference Series, 2013, 471, 012012.	0.4	2
121	Quantitative study of the interfacial intermixing and segregation effects across the wetting layer of Ga(As,Sb)-capped InAs quantum dots. Applied Physics Letters, 2012, 101, .	3.3	4
122	Cubic MnSb: Epitaxial growth of a predicted room temperature half-metal. Physical Review B, 2012, 85, .	3.2	50
123	Influence of charged-dislocation density variations on carrier mobility in heteroepitaxial semiconductors: The case of SnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>on sapphire. Physical Review B, 2012, 86, .	3.2	14
124	Relaxation dynamics and residual strain in metamorphic AlSb on GaAs. Applied Physics Letters, 2012, 100, .	3.3	9
125	Bow Free 4'' Diameter 3C-SiC Epilayers Formed upon Wafer-Bonded Si/SiC Substrates. ECS Solid State Letters, 2012, 1, P85-P88.	1.4	5
126	A simple approach to characterizing block copolymer assemblies: graphene oxide supports for high contrast multi-technique imaging. Soft Matter, 2012, 8, 3322.	2.7	65

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127	Toward All-Oxide Magnetic Tunnel Junctions: Epitaxial Growth of SrRuO₃/CoFe₂O₄/La_{2/3}Sr_{1/3}MnO₃3.0 Trilayers. Crystal Growth and Design, 2012, 12, 954-959.		15
128	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	31.5	65
129	Enhanced infrared photo-response from GaSb/GaAs quantum ring solar cells. Applied Physics Letters, 2012, 101, 231101.	3.3	29
130	Forest cover and deforestation patterns in the Northern Andes (Lake Maracaibo Basin): A synoptic assessment using MODIS and Landsat imagery. Applied Geography, 2012, 35, 152-163.	3.7	44
131	Optical observation of single-carrier charging in type-II quantum ring ensembles. Applied Physics Letters, 2012, 100, .	3.3	41
132	High-Resolution Electron Microscopy of Semiconductor Heterostructures and Nanostructures. Springer Series in Materials Science, 2012, , 23-62.	0.6	2
133	Structural characterization of GaSb-capped InAs/GaAs quantum dots with a GaAs intermediate layer. Materials Letters, 2011, 65, 1608-1610.	2.6	4
134	Memetic algorithms based on local search chains for large scale continuous optimisation problems: MA-SSW-Chains. Soft Computing, 2011, 15, 2201-2220.	3.6	88
135	A test for the homoscedasticity of the residuals in fuzzy rule-based forecasters. Applied Intelligence, 2011, 34, 386-393.	5.3	5
136	Physical Vapor Deposition of Metal Nanoparticles on Chemically Modified Graphene: Observations on Metalâ€“Graphene Interactions. Small, 2011, 7, 3202-3210.	10.0	109
137	Metamorphic antimonides on GaAs for thermophotovoltaic devices. , 2011, , .		0
138	Structural Origin of Enhanced Luminescence Efficiency of Antimony Irradiated InAs Quantum Dots. Advanced Science Letters, 2011, 4, 3776-3778.	0.2	0
139	Theoretical modelling of quaternary GaInAsSb/GaAs self-assembled quantum dots. Journal of Physics: Conference Series, 2010, 245, 012081.	0.4	4
140	Lateral absorption measurements of InAs/GaAs quantum dots stacks: Potential as intermediate band material for high efficiency solar cells. Energy Procedia, 2010, 2, 27-34.	1.8	2
141	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mstyle		

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145	Publisher's Note: Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots [Phys. Rev. B82, 235316 (2010)]. Physical Review B, 2010, 82, .	3.2	0
146	Reducing carrier escape in the InAs/GaAs quantum dot intermediate band solar cell. Journal of Applied Physics, 2010, 108, .	2.5	156
147	Blocking of indium incorporation by antimony in IIIâ€“V-Sb nanostructures. Nanotechnology, 2010, 21, 145606.	2.6	16
148	Photoluminescence of InAs0.926Sb0.063N0.011/InAs multi-quantum wells in the mid-infrared spectral range. Journal Physics D: Applied Physics, 2010, 43, 345103.	2.8	7
149	Correlation between defect density and current leakage in InAsâ•GaAs quantum dot-in-well structures. Journal of Applied Physics, 2009, 106, .	2.5	16
150	Optical polarization anisotropy of a-plane GaN/AlGaN multiple quantum well structures grown on r-plane sapphire substrates. Journal of Applied Physics, 2009, 105, 123112.	2.5	24
151	Hybrid crossover operators with multiple descendents for real-coded genetic algorithms: Combining neighborhood-based crossover operators. International Journal of Intelligent Systems, 2009, 24, 540-567.	5.7	22
152	Optical polarisation anisotropy in a â€plane GaN/AlGaN multiple quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S523.	0.8	2
153	Growth of ScN epitaxial films by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 2054-2057.	1.5	19
154	Real-parameter crossover operators with multiple descendents: An experimental study. International Journal of Intelligent Systems, 2008, 23, 246-268.	5.7	8
155	Properties of non-polar a-plane GaN/AlGaN quantum wells. Journal of Crystal Growth, 2008, 310, 4983-4986.	1.5	20
156	Carrier recombination effects in strain compensated quantum dot stacks embedded in solar cells. Applied Physics Letters, 2008, 93, 123114.	3.3	46
157	Stress compensation by GaP monolayers for stacked InAs/GaAs quantum dots solar cells. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	0
158	Optical properties of GaN/AlGaN quantum wells grown on nonpolar substrates. Applied Physics Letters, 2008, 93, 101901.	3.3	34
159	Quantum dots in strained layersâ€”preventing relaxation through the precipitate hardening effect. Journal of Applied Physics, 2008, 104, .	2.5	9
160	Structural analysis of life tested 1.3â€‚Î¼m quantum dot lasers. Journal of Applied Physics, 2008, 103, .	2.5	45
161	Electron tomography using compositional-sensitive diffraction contrast for 3D characterization of self-assembled semiconductor quantum dots. Microscopy and Microanalysis, 2008, 14, 1052-1053.	0.4	0
162	TEM characterization of InAs/GaAs quantum dots capped by a GaSb/GaAs layer. , 2008, , 45-46.		0

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163	A TEM study of the evolution of InAs/GaAs self-assembled dots on (3â€‰1â€‰1)B GaAs with growth interruption. Semiconductor Science and Technology, 2007, 22, 168-170.	2.0	3
164	Structural, magnetic, and transport properties of Fe3O4âˆ•Si(111) and Fe3O4âˆ•Si(001). Journal of Applied Physics, 2007, 101, 123903.	2.5	45
165	Configuration of the misfit dislocation networks in uncapped and capped InN quantum dots. Applied Physics Letters, 2007, 91, 071915.	3.3	12
166	Ferroelectric parallel-plate capacitors with copper electrodes for high-frequency applications. Applied Physics Letters, 2007, 91, 252902.	3.3	12
167	Effects of spacer growth temperature on the optical properties of quantum dot laser structures. , 2007, , .		0
168	Incorporation of Sb in InAsâˆ•GaAs quantum dots. Applied Physics Letters, 2007, 91, 263105.	3.3	29
169	Strain Mapping at the Atomic Scale in Highly Mismatched Heterointerfaces. Advanced Functional Materials, 2007, 17, 2588-2593.	14.9	12
170	The Peak Pairs algorithm for strain mapping from HRTEM images. Ultramicroscopy, 2007, 107, 1186-1193.	1.9	230
171	Strain Relief Analysis of InN Quantum Dots Grown on GaN. Nanoscale Research Letters, 2007, 2, 442-6.	5.7	14
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